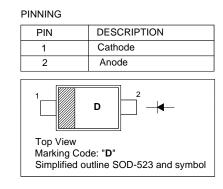
SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

for high speed switching and detection applications

Features

- Small surface mounting type
- · Low reverse current and low forward voltage
- High reliability



Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V _{RM}	40	V
Reverse Voltage	V _R	30	V
Mean Rectifying Current	Ι _ο	30	mA
Peak Forward Surge Current (60 Hz, 1 Cycle)	I _{FSM}	200	mA
Junction Temperature	Tj	125	°C
Storage Temperature Range	Ts	- 40 to + 125	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Тур.	Max.	Unit
Forward Voltage at I _F = 1 mA	V_{F}	-	0.37	V
Reverse Current at $V_R = 30 V$	I _R	-	0.5	μA
Capacitance Between Terminals at $V_R = 1 V$, f = 1 MHz	C _T	2	-	pF

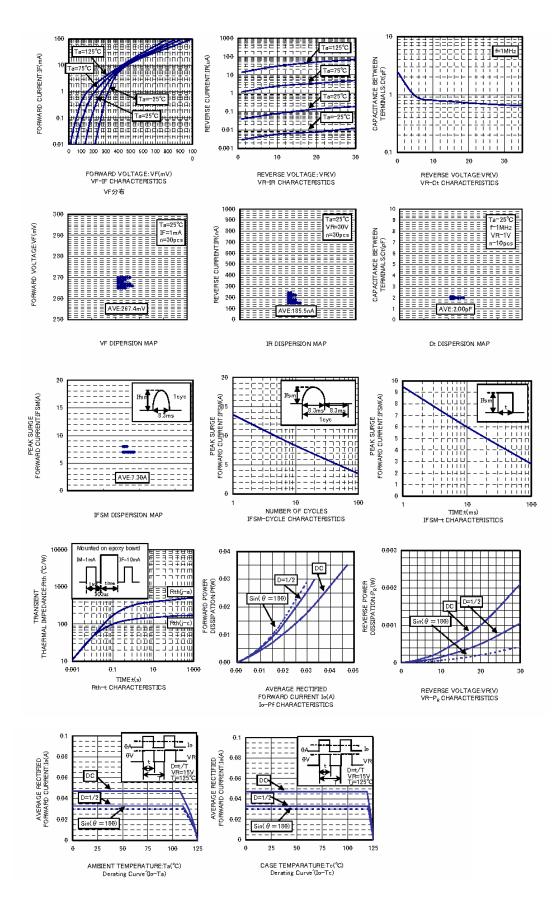
Note: ESD sensitive product handling required.







Dated : 23/11/2006





SEMTECH ELECTRONICS LTD.

(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)



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PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

ALL ROUND ∢ H_E D -(A) q ш С Е V UNIT D H_{E} bp А Ζ 0.70 0.60 0.4 0.135 1.25 0.85 1.7 0.1 5° mm 0.3 0.127 1.15 0.75 1.5







SOD-523

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